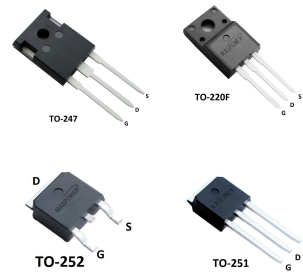


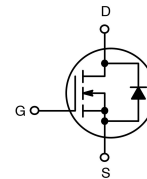
features

- Low gate charge (typical 12nC)
- Low Crss (typical 5.5pF)
- 100% avalanche tested
- Fast switching
- Improved dv/dt capability



Applications

- Switching application



Electrical ratings

Absolute maximum ratings

Parameter	Symbol	Value	Unit
Drain-source voltage ($V_{GS}=0$)	V_{DS}	1000	V
Gate-source voltage	V_{GS}	± 30	
Drain current (continuous) at $TC=25^{\circ}C$	I_D	3	A
Drain current (continuous) at $TC=100^{\circ}C$	I_D	2.1	
Drain current (pulsed)	I_{DM}	12	A
Avalanche current repetitive or not-repetitive (pulse width limited by T_j Max)	IAR	3	A
Single pulse avalanche energy (starting $T_j=25^{\circ}C$ $I_D=I_{AR}$ $V_{DD}=50V$)	EAS	300	mJ
Total dissipation at $TC=25^{\circ}C$ (TO-247)	PD	272	W
Total dissipation at $TC=25^{\circ}C$ (TO-252/TO-251)	PD	50	W
Drain source ESD (HBM-C=100pF, R=1.5KΩ)	$V_{ESD(GS)}$	4000	V
Peak diode recovery voltage slope	dv/dt	4.5	V/ns
Insulation withstand voltage(RMS)from all three leads to external heat sink ($t=1s$ $TC=25^{\circ}C$)	V_{ISO}	2500	v
Operating junction temperature	T_J	-55 to 175	$^{\circ}C$
Storage temperature	T_{STG}		

Electrical characteristics ($T_{CASE}=25^{\circ}C$ unless otherwise specified)

On/off states

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Drain-source breakdown voltage	V(BR)DSS	ID=1mA VGS=0	1000	-	-	V
Zero gate voltage drain current (VGS=0)	IDSS	VDS=Max rating	-	-	1	μA
		TC=125°C	-	-	100	μA
Gate body leakage current (VGS=0)	IGSS	VGS=±30V	-	-	±100	nA
Gate threshold voltage	VGS(th)	VDS=VGS ID=100μA	3.0	4.0	5.0	V
Static drain-source on resistance	RDS(on)	VGS=10V ID=1A	-	5.2	5.8	Ω

Dynamic

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Forward transconductance	gfs	VDS = 15 V, ID = 1.75A	-	3	-	S
Input capacitance	Ciss	VDS=25V, f=1MHz, VGS=0	-	390	500	pF
Output capacitance	Coss		-	45	60	
Reverse transfer capacitance	Crss		-	5.5	7.0	
Total gate charge	Qg	VDD=800V, ID=3A VGS=10V	-	12	15	nC
Gate-source charge	Qgs		-	2.8	-	
Gate-drain charge	Qgd		-	6.1	-	
Turn-on delay time	td(on)	VDD = 500V, ID = 3A, RG = 25 Ω, VGS = 10 V	-	15	40	ns
Rise time	tr		-	35	80	
Turn-off-delay time	td(off)		-	20	50	
Fall time	tf		-	30	70	

Source Drain Diode

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Source Drain Current	ISD		-	-	3	A
Source Drain Current(Pulsed)	ISDM		-	-	12	A
Forward On Voltage	VSD	ISD=3A, VGS=0V	-	-	1.2	V
Reverse Recovery Time	Trr	ISD=3A, di/dt=100A/μS	-	400	-	ns
Reverse Recovery Charge	Qrr	ISD=3A, di/dt=100A/μS	-	1.6	-	μC

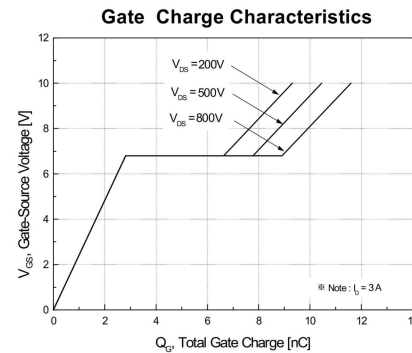
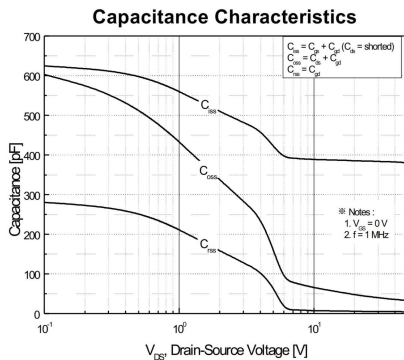
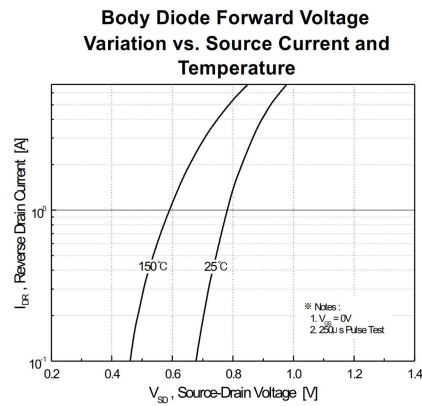
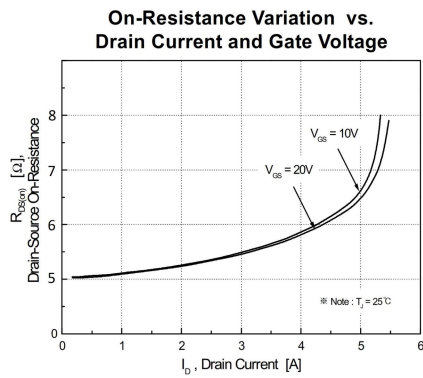
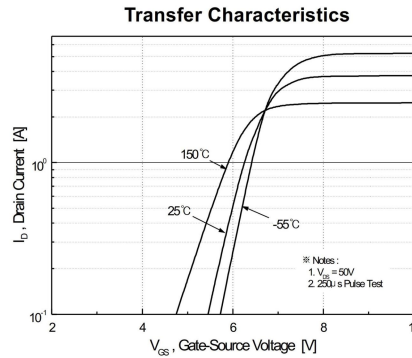
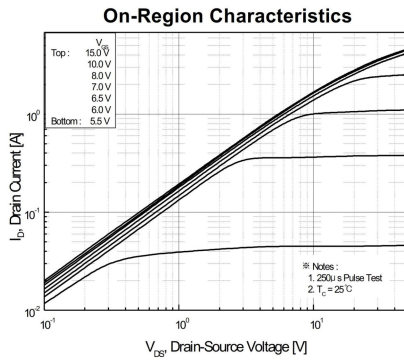
Thermal data

Parameter	Symbol	Value	Unit
Thermal resistance junction max(TO-247)	Rthj-case	0.46	°C/W
Thermal resistance junction max(TO-252)	Rthj-case	2.5	°C/W

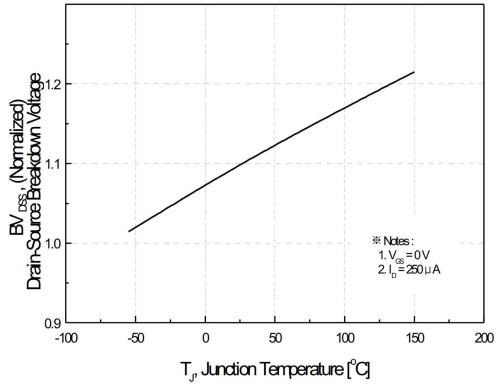
Order codes

Partnumber	Marking	Package
MS3N100HGC0	MS3N100HGC0	TO-247
MS3N100HGD0	MS3N100HGD0	TO-252
MS3N100HGT1	MS3N100HGT1	TO-220F
MS3N100HGD1	MS3N100HGD1	TO-251

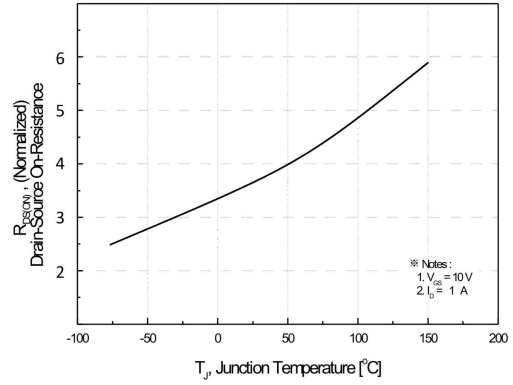
Electrical characteristics (curves)



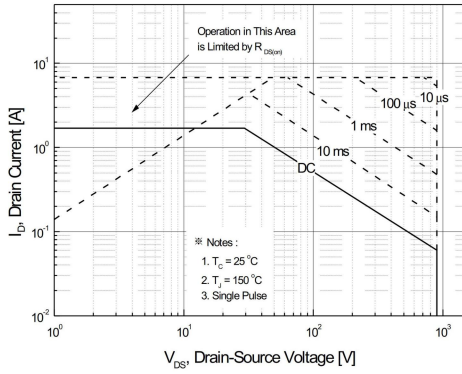
Breakdown Voltage Variation vs. Temperature



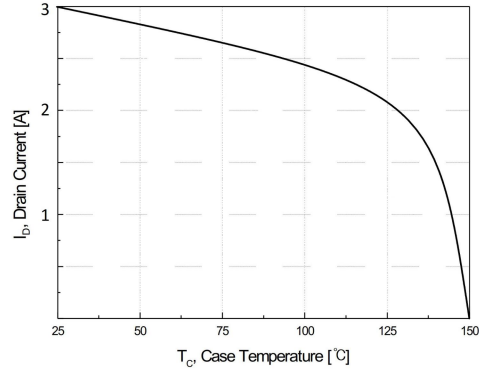
On-Resistance Variation vs. Temperature



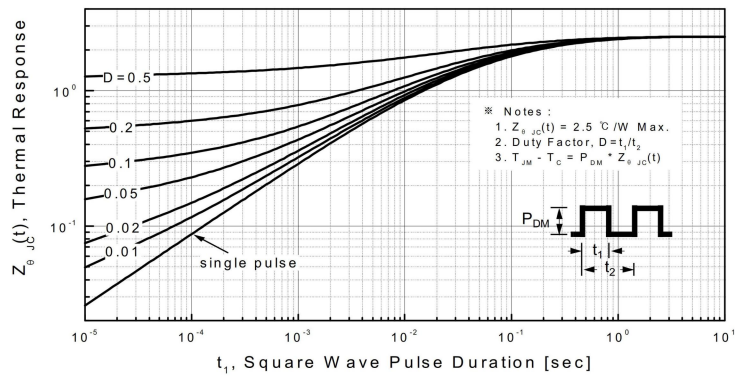
Maximum Safe Operating Area



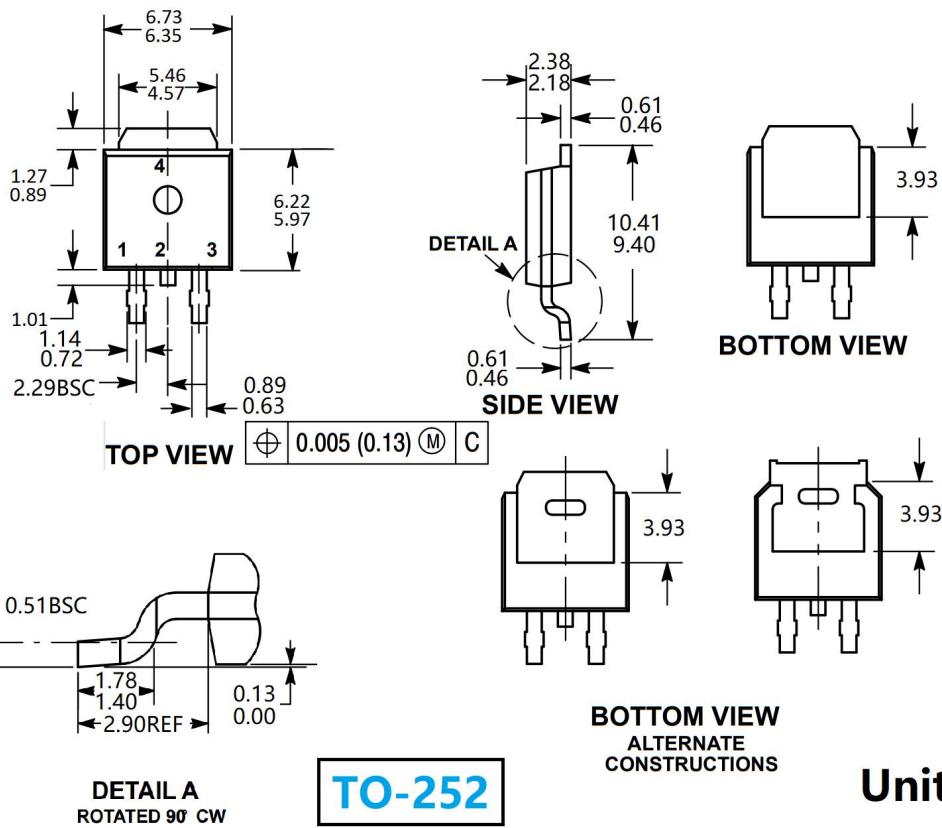
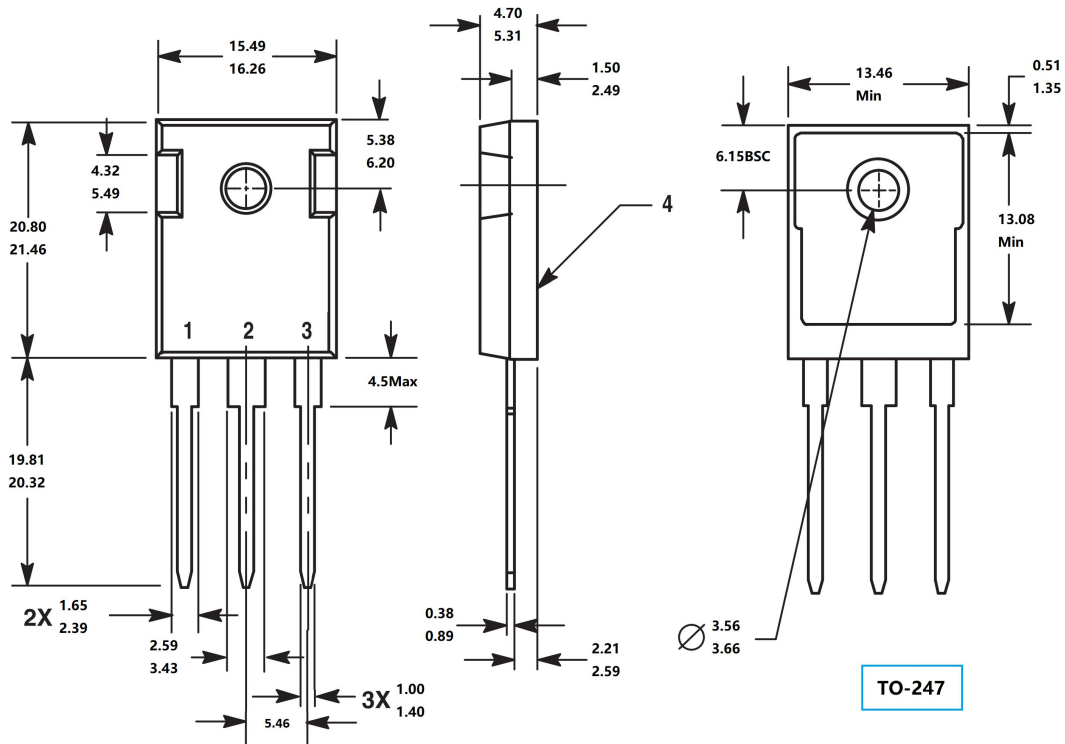
Maximum Drain Current vs. Case Temperature

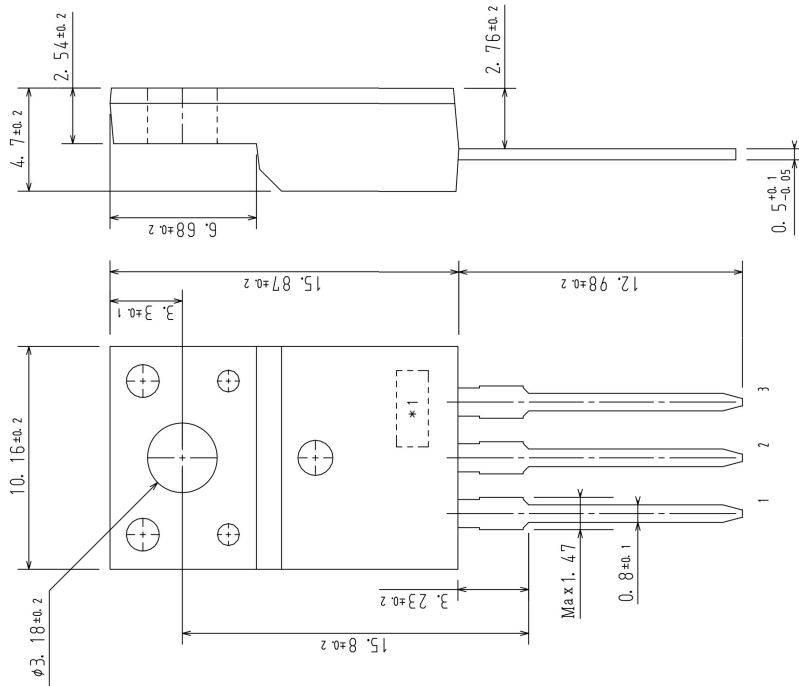


Transient Thermal Response Curve



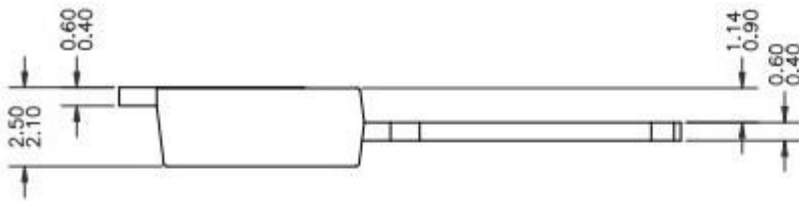
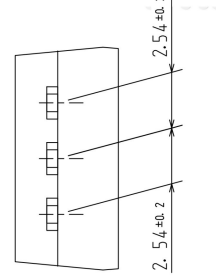
Package outline dimension





Uint: mm

TO-220F



TO-251

